

HiPerFET™

Power MOSFETs

ISOPLUS247™, Q-Class

IXFR 44N50Q

IXFR 48N50Q

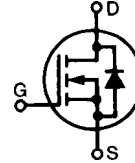
V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	34 A	120 mΩ
500 V	40 A	110 mΩ

(Electrically Isolated Backside)

$t_{rr} \leq 250$ ns

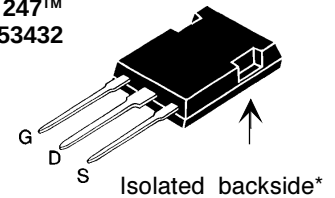
N-Channel Enhancement Mode

Avalanche Rated, Low Q_g , High dv/dt



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	500		V
V_{GS}	Continuous	±20		V
V_{GSM}	Transient	±30		V
I_{D25}	$T_C = 25^\circ\text{C}$	44N50Q	34	A
		48N50Q	40	A
I_{DM}	$T_C = 25^\circ\text{C}$, Note 1	44N50Q	176	A
		48N50Q	192	A
I_{AR}	$T_C = 25^\circ\text{C}$	44N50Q	44	A
		48N50Q	48	A
E_{AR}	$T_C = 25^\circ\text{C}$	60		mJ
E_{AS}	$T_C = 25^\circ\text{C}$	2.5		J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5		V/ns
P_D	$T_C = 25^\circ\text{C}$	310		W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	1.6 mm (0.063 in.) from case for 10 s	300		°C
V_{ISOL}	50/60 Hz, RMS $t = 1$ min	2500		V~
Weight		5		g

ISOPLUS 247™
E153432



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low drain to tab capacitance(<30pF)
- IXYS advanced low Q_g process
- Rugged polysilicon gate cell structure
- Rated for Unclamped Inductive Load Switching (UIS)
- Fast intrinsic diode

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

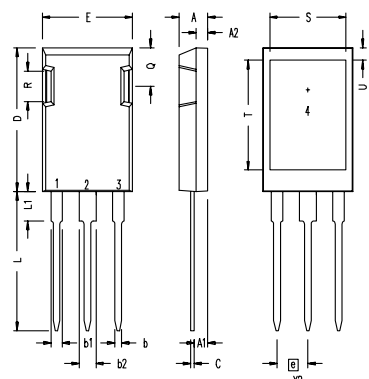
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$			±100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V			100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = I_T$ Notes 2, 3	44N50Q		120 mΩ
		48N50Q		110 mΩ

Symbol	Test Conditions		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
			min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$	Notes 2, 3	30	45	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$			6400	pF
C_{oss}				930	pF
C_{rss}				220	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External), Notes 2, 3			33	ns
t_r				22	ns
$t_{d(off)}$				75	ns
t_f				10	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ Notes 2, 3			190	nC
Q_{gs}				40	nC
Q_{gd}				86	nC
R_{thJC}				0.40	K/W
R_{thCK}				0.15	K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			48 A
I_{SM}	Repetitive; Note 1			192 A
V_{SD}	$I_F = I_T, V_{GS} = 0\text{ V}$, Notes 2, 3			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
Q_{RM}				1.4 μC
I_{RM}				10 A

- Note: 1. Pulse width limited by T_{JM}
 2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$
 3. IXFR44N50Q: $I_T = 22\text{ A}$
 IXFR48N50Q: $I_T = 24\text{ A}$

ISOPLUS247 OUTLINE



1 Gate, 2 Drain (Collector)
 3 Source (Emitter)
 4 no connection

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L ₁	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190